



40V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} MAX	I _{D MAX} T _C = +25°C
-40V	$10m\Omega$ @ $V_{GS} = -10V$	-76A
	$14m\Omega @ V_{GS} = -4.5V$	-58A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

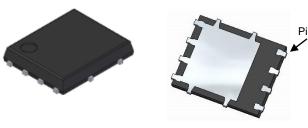
- DC-DC Converters
- **Power Management Functions**
- Analog Switch

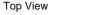
Features and Benefits

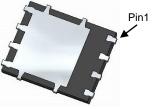
- 100% Unclamped Inductive Switch (UIS) Test In Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP4011SPSQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)







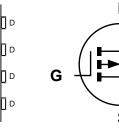
Bottom View

Top View Pin Configuration

s [

sΓ

G [



Internal Schematic

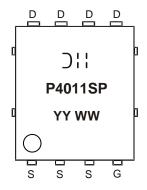
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP4011SPSQ -13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ = Manufacturer's Marking P4011SP = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019)WW = Week (01 to 53)

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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Brain Comment V 40V (Nata 7)	Steady	T _C = +25°C	- I _D	-76	A
Continuous Drain Current V _{GS} = -10V (Note 7)	State	T _C = +70°C		-61	
Continuous Dusis Courset V 40V (Note C)	Steady State	T _A = +25°C	I _D	-11.7	А
Continuous Drain Current V _{GS} = -10V (Note 6)		T _A = +70°C		-9.4	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-300	Α		
Maximum Body Diode Continuous Current (Note 6)	I _S	-8.9	Α		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%	ulsed Source Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	-300	Α
Avalanche Current (Note 8) L = 1mH	I _{AS}	-22	А		
Avalanche Energy (Note 8) L = 1mH			E _{AS}	250	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

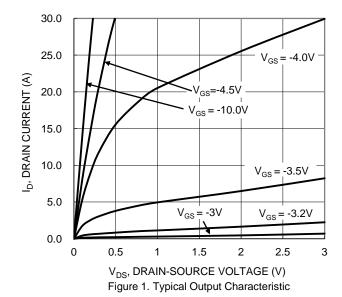
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	96.4	°C/W
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P _D	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	55	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{0JC}	1.3	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV_{DSS}	-40			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}			-1	μΑ	$V_{DS} = -32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-1.9	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	6	10	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	10	14	11177	$V_{GS} = -4.5V, I_D = -9.8A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1	V	V _{GS} = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		2747	_		V _{DS} = -20V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	508	_	pF		
Reverse Transfer Capacitance	C_{rss}	_	222	_			
Gate Resistance	Rg	_	21.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	25				
Total Gate Charge (V _{GS} = -10V)	Q_g	_	52	_	nC	V 00V I 0.0A	
Gate-Source Charge	Q _{gs}	_	8.5	_	nc nc	$V_{DS} = -20V, I_{D} = -9.8A$	
Gate-Drain Charge	Q _{qd}	_	11.8	_			
Turn-On Delay Time	t _{D(ON)}	_	6.6	_			
Turn-On Rise Time	t _R	_	6.5	_		$V_{GS} = -10V, V_{DD} = -20V$	
Turn-Off Delay Time	t _{D(OFF)}	_	222	_	ns	$R_g = 6\Omega$, $I_D = -1A$	
Turn-Off Fall Time	t _F		138	_			
Reverse Recovery Time	t _{RR}		25	_	ns	I _F = -9.8A, di/dt = -100A/μs	
Reverse Recovery Charge	Q_{RR}		17	_	nC	I _F = -9.8A, di/dt = -100A/µs	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- Ins and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





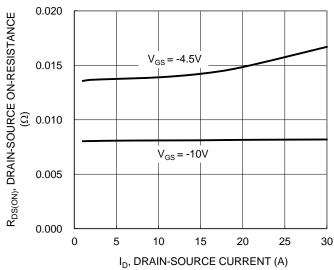


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

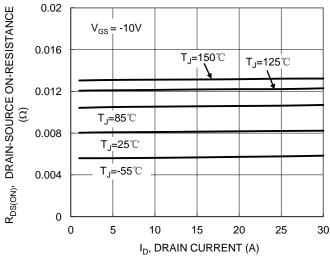


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

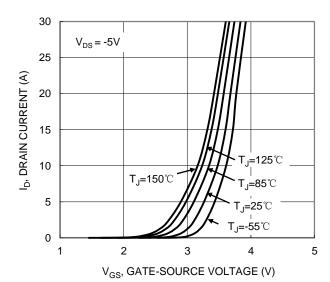


Figure 2. Typical Transfer Characteristic

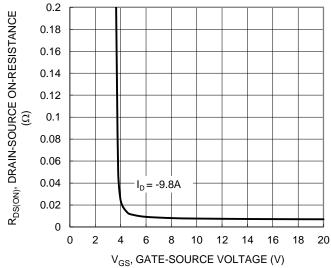


Figure 4. Typical Transfer Characteristic

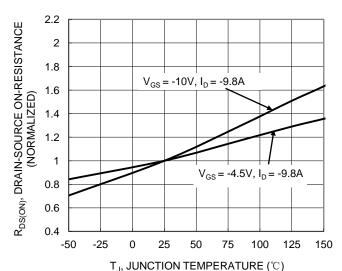


Figure 6. On-Resistance Variation with Temperature



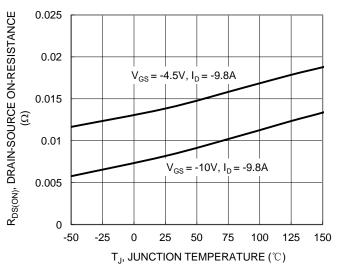


Figure 7. On-Resistance Variation with Temperature

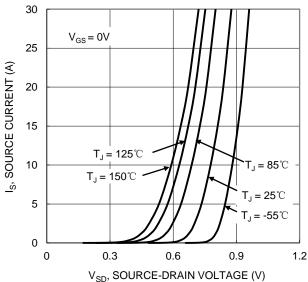


Figure 9. Diode Forward Voltage vs. Current

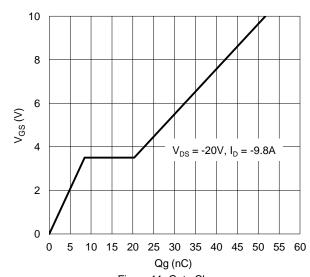


Figure 11. Gate Charge

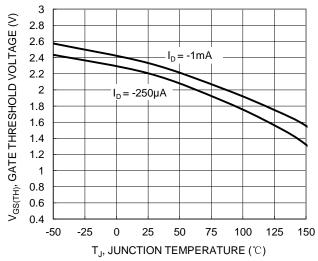


Figure 8. Gate Threshold Variation vs. Junction Temperature

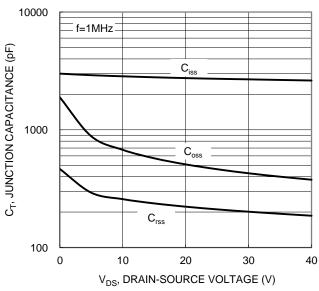


Figure 10. Typical Junction Capacitance

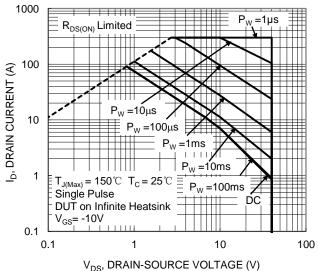


Figure 12. SOA, Safe Operation Area



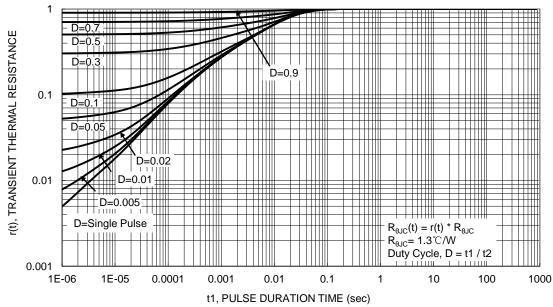


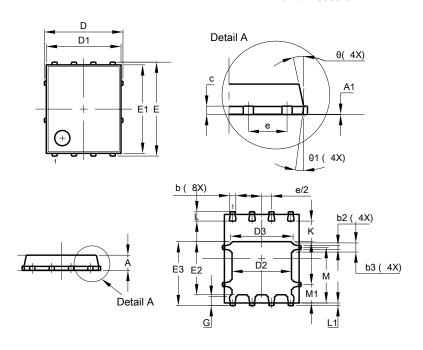
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

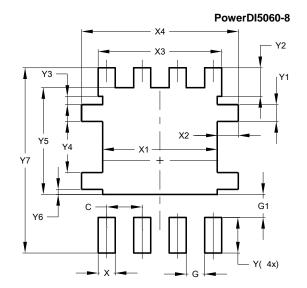
PowerDI5060-8



PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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